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Microsemi.

Power Matters[™]

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Overview Diagrams

| Symbol | Min | Тур | Max | Unit |
|----------------------|----------------------|----------------------|----------------------|---------------------------|
| V _{CE(sat)} | | | 1.50 | V |
| HFE | 10.00 | | 40.00 | |
| | V _{CE(sat)} | V _{CE(sat)} | V _{CE(sat)} | V _{CE(sat)} 1.50 |

| Maximum Electrical Rating | Symbol | Min | Тур | Max | Unit |
|--|----------------------|-----|-----|--------|------|
| Breakdown Voltage, Collector-Base (Emitter Open) | V _{BR(CBO)} | | | 650.00 | V |
| Collector Current (dc) | I _C | | | 8.00 | А |
| Collector-Emitter Voltage (Base Open) | V_{CEO} | | | 400.00 | V |
| Emitter-Base Voltage (Collector Open) | V _{EBO} | | | 7.00 | V |
| Power Dissipation, Total | P _T | | | 150.00 | W |

This part can be found in the following product categories:

- → Discretes → Transistors → BJT(BiPolar Junction Transistor) → PNP Transistor

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